

CR8KM-12A

Thyristor

Medium Power Use

REJ03G0388-0100

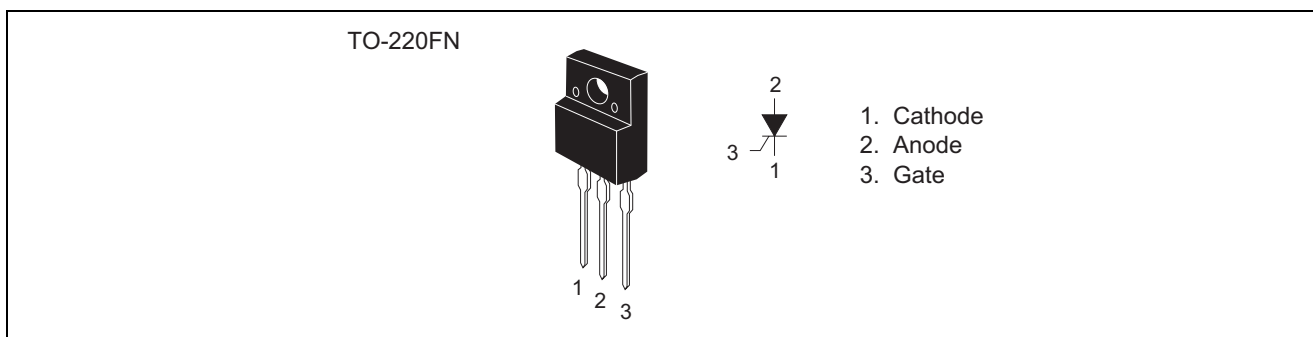
Rev.1.00

Aug.06.2004

Features

- $I_{T(AV)}$: 8 A
- V_{DRM} : 600 V
- I_{GT} : 15 mA
- V_{iso} : 2000 V
- Insulated Type
- Planar Passivation Type
- UL Recognized : Yellow Card No. E223904
File No. E80271

Outline



Applications

Switching mode power supply, regulator for autcycle, motor control, heater control, and other general purpose control applications

Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		12	
Repetitive peak reverse voltage	V_{RRM}	600	V
Non-repetitive peak reverse voltage	V_{RSM}	720	V
DC reverse voltage	$V_{R(DC)}$	480	V
Repetitive peak off-state voltage	V_{DRM}	600	V
DC off-state voltage	$V_{D(DC)}$	480	V

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_T (RMS)$	12.6	A	
Average on-state current	$I_T (AV)$	8	A	Commercial frequency, sine half wave 180° conduction, $T_c = 81^\circ\text{C}$
Surge on-state current	I_{TSM}	120	A	60Hz sine half wave 1 full cycle, peak value, non-repetitive
I^2t for fusing	I^2t	60	A^2s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P_{GM}	5	W	
Average gate power dissipation	$P_{G (AV)}$	0.5	W	
Peak gate forward voltage	V_{FGM}	6	V	
Peak gate reverse voltage	V_{RGM}	10	V	
Peak gate forward current	I_{FGM}	2	A	
Junction temperature	T_j	– 40 to +125	$^\circ\text{C}$	
Storage temperature	T_{stg}	– 40 to +125	$^\circ\text{C}$	
Mass	—	2.0	g	Typical value
Isolation voltage	V_{iso}	2000	V	$T_a = 25^\circ\text{C}$, AC 1 minute, each terminal to case

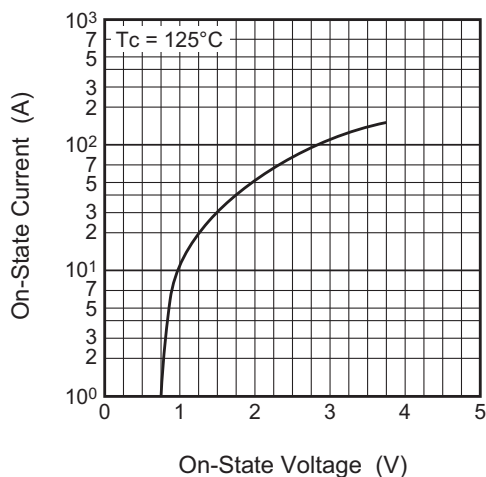
Electrical Characteristics

Parameter	Symbol	Minimum Characteristics Value			Unit	Test conditions
		Min.	Typ.	Max.		
Repetitive peak reverse current	I_{RRM}	—	—	2.0	mA	$T_j = 125^\circ\text{C}$, V_{RRM} applied
Repetitive peak off-state current	I_{DRM}	—	—	2.0	mA	$T_j = 125^\circ\text{C}$, V_{DRM} applied
On-state voltage	V_{TM}	—	—	1.4	V	$T_c = 25^\circ\text{C}$, $I_{TM} = 25\text{ A}$, instantaneous value
Gate trigger voltage	V_{GT}	—	—	1.0	V	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $I_T = 1\text{ A}$
Gate non-trigger voltage	V_{GD}	0.2	—	—	V	$T_j = 125^\circ\text{C}$, $V_D = 1/2 V_{DRM}$
Gate trigger current	I_{GT}	—	—	15	mA	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $I_T = 1\text{ A}$
Holding current	I_H	—	15	—	mA	$T_j = 25^\circ\text{C}$, $V_D = 12\text{ V}$
Thermal resistance	$R_{th (j-c)}$	—	—	3.7	$^\circ\text{C/W}$	Junction to case ^{Note1}

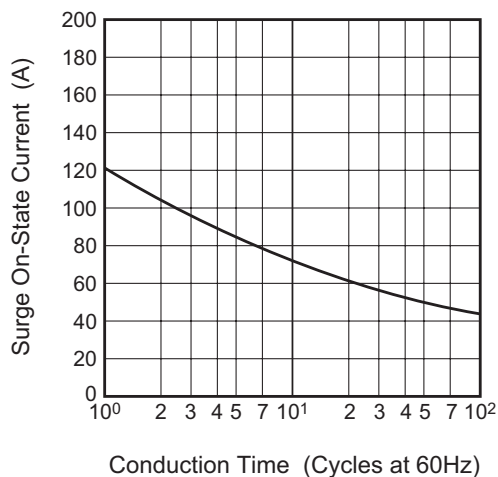
Notes: 1. The contact thermal resistance $R_{th (c-f)}$ in case of greasing is 0.5°C/W .

Performance Curves

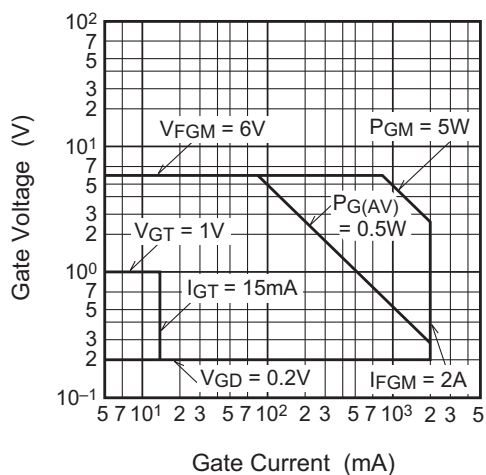
Maximum On-State Characteristics



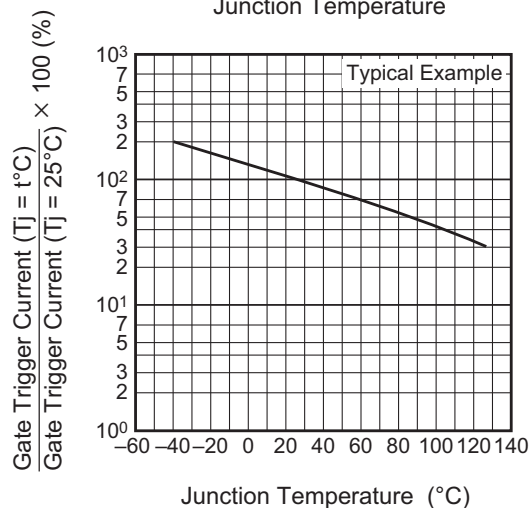
Rated Surge On-State Current



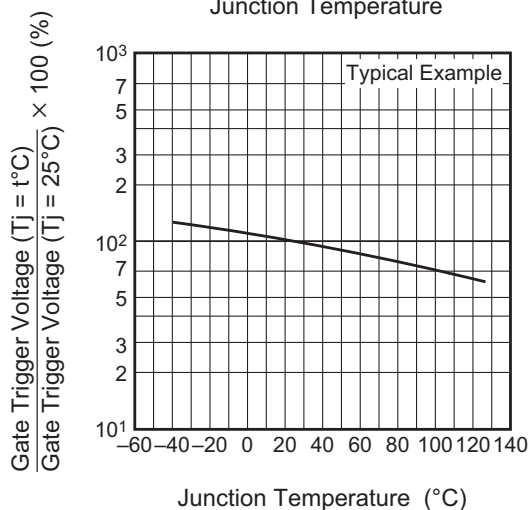
Gate Characteristics



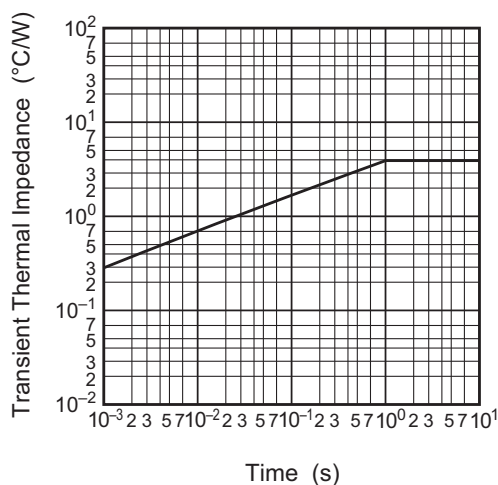
Gate Trigger Current vs. Junction Temperature

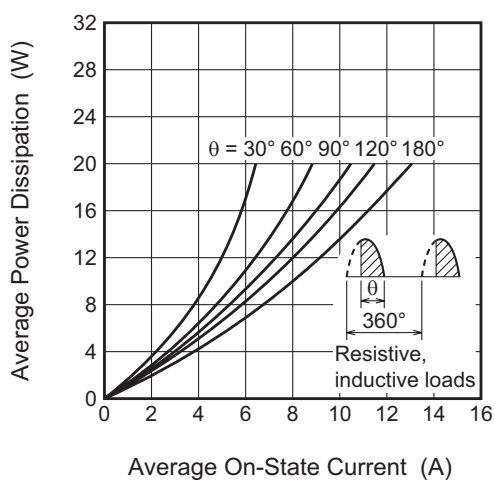
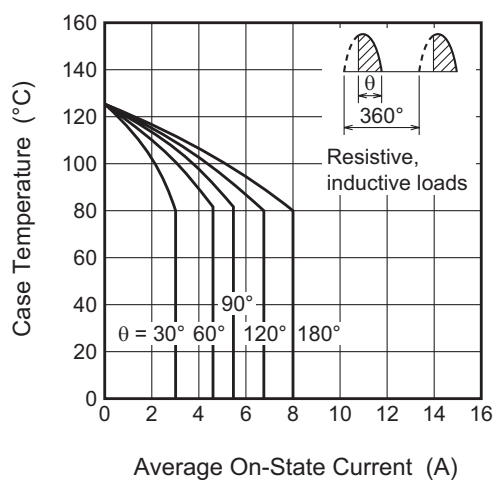
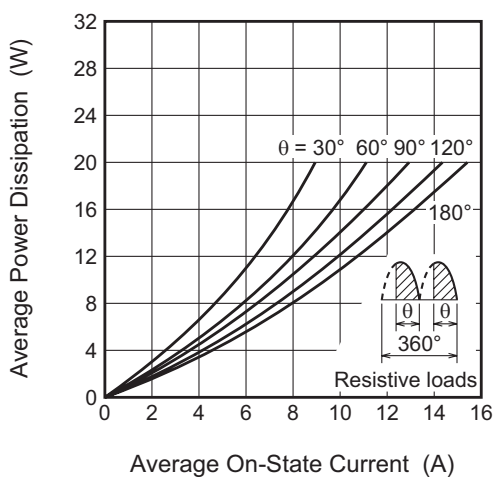
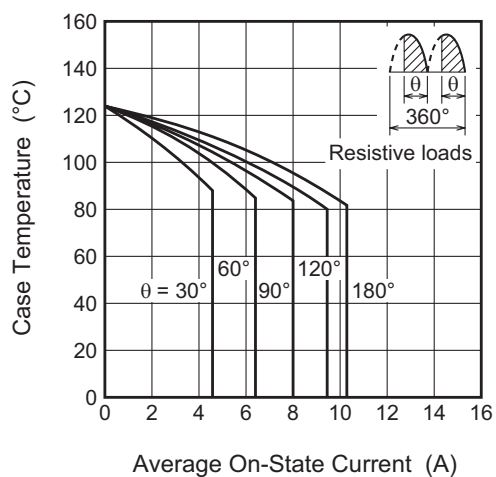
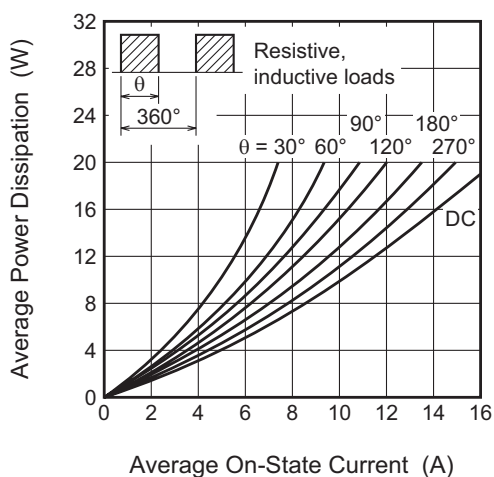
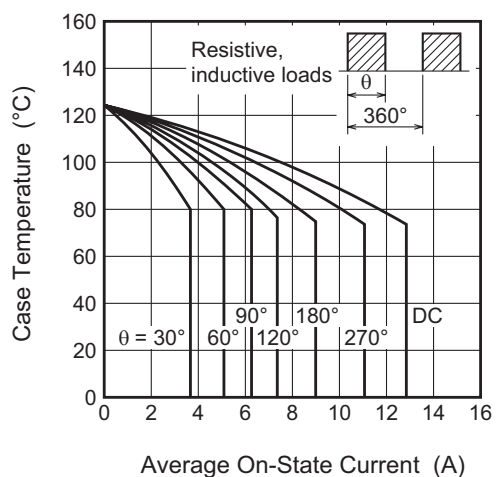


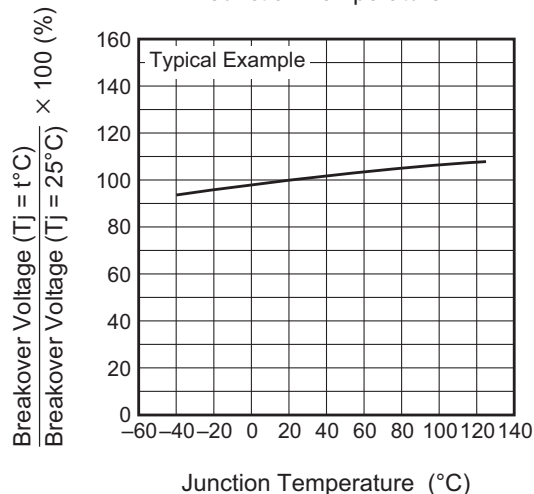
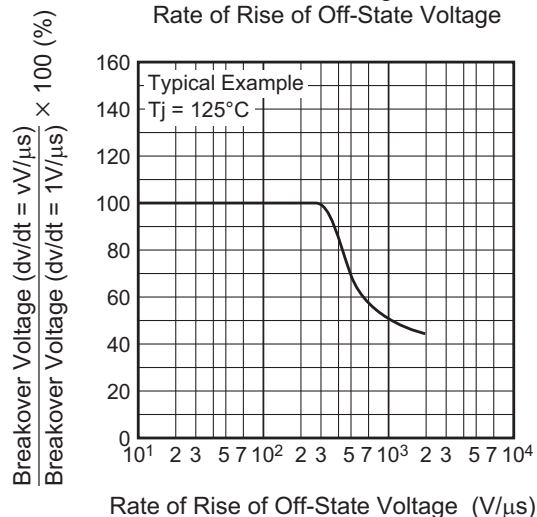
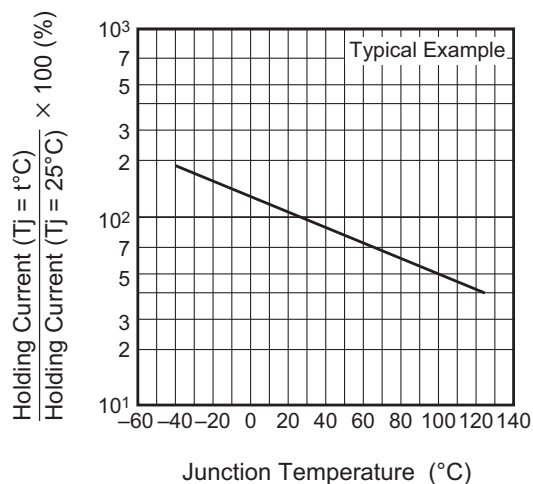
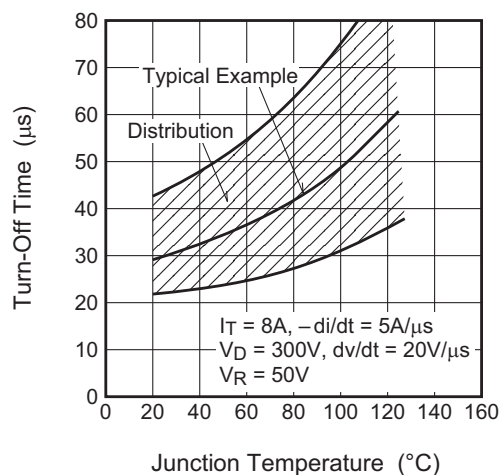
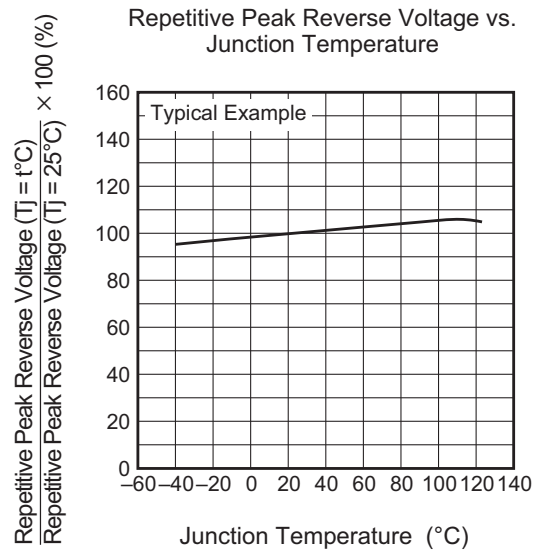
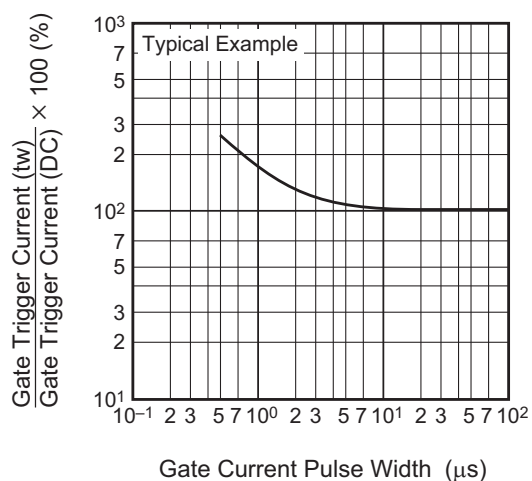
Gate Trigger Voltage vs. Junction Temperature



Maximum Transient Thermal Impedance Characteristics (Junction to case)



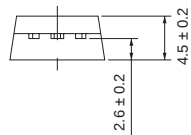
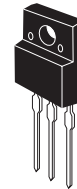
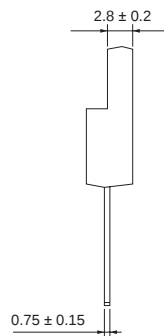
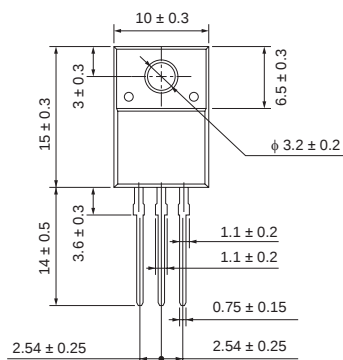
Maximum Average Power Dissipation
(Single-Phase Half Wave)Allowable Case Temperature vs.
Average On-State Current
(Single-Phase Half Wave)Maximum Average Power Dissipation
(Single-Phase Full Wave)Allowable Case Temperature vs.
Average On-State Current
(Single-Phase Full Wave)Maximum Average Power Dissipation
(Rectangular Wave)Allowable Case Temperature vs.
Average On-State Current
(Rectangular Wave)

Breakover Voltage vs.
Junction TemperatureBreakover Voltage vs.
Rate of Rise of Off-State VoltageHolding Current vs.
Junction TemperatureTurn-Off Time vs.
Junction TemperatureRepetitive Peak Reverse Voltage vs.
Junction TemperatureGate Trigger Current vs.
Gate Current Pulse Width

Package Dimensions

TO-220FN

EIAJ Package Code	JEDEC Code	Mass (g) (reference value)	Lead Material
—	—	2.0	Cu alloy



Note 1) The dimensional figures indicate representative values unless otherwise the tolerance is specified.

Symbol	Dimension in Millimeters		
	Min	Typ	Max
A	—	—	—
A ₁	—	—	—
A ₂	—	—	—
b	—	—	—
D	—	—	—
E	—	—	—
e	—	—	—
x	—	—	—
y	—	—	—
y ₁	—	—	—
ZD	—	—	—
ZE	—	—	—

Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Plastic Magazine (Tube)	50	Type name	CR8KM-12A
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	CR8KM-12A-A8

Note : Please confirm the specification about the shipping in detail.

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